

### 256K-BIT CMOS STATIC RAM

### 32K-WORD BY 8-BIT

### EXTENDED TEMPERATURE OPERATION

#### Description

The  $\mu$ PD43256B-X is a high speed, low power, and 262,144 bits (32,768 words by 8 bits) CMOS static RAM.

The  $\mu$ PD43256B-X is an extended-operating-temperature version of the  $\mu$ PD43256B (X version :  $T_A = -25$  to  $+85^\circ\text{C}$ ).

And A and B versions are low voltage operations. Battery backup is available.

The  $\mu$ PD43256B-X is packed in 28-pin PLASTIC TSOP (I) (8 x 13.4 mm).

#### Features

- 32,768 words by 8 bits organization
- Fast access time: 70, 85, 100, 120, 150 ns (MAX.)
- Operating ambient temperature:  $T_A = -25$  to  $+85^\circ\text{C}$
- Low voltage operation (A version:  $V_{CC} = 3.0$  to  $5.5$  V, B version:  $V_{CC} = 2.7$  to  $5.5$  V)
- Low  $V_{CC}$  data retention: 2.0 V (MIN.)
- /OE input for easy application

Part number	Access time ns (MAX.)	Operating supply voltage V	Operating ambient temperature $^\circ\text{C}$	Supply current		
				At operating mA (MAX.)	At standby $\mu\text{A}$ (MAX.)	At data retention $\mu\text{A}$ (MAX.) <sup>Note1</sup>
$\mu$ PD43256B-xxX	70, 85	4.5 to 5.5	-25 to +85	45	50	2
$\mu$ PD43256B-AxxX	85 <sup>Note2</sup> , 100, 120 <sup>Note2</sup>	3.0 to 5.5				
$\mu$ PD43256B-BxxX <sup>Note2</sup>	100, 150 <sup>Note2</sup>	2.7 to 5.5		40		

**Notes 1.**  $T_A \leq 40^\circ\text{C}$ ,  $V_{CC} = 3.0$  V

**2.** 100 ns (MAX.) ( $V_{CC} = 4.5$  to  $5.5$  V)

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Ordering Information

Part number	Package	Access time ns (MAX.)	Operating supply voltage V	Operating ambient temperature °C	Remark	
μPD43256BGW-70X-9JL	28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)	70	4.5 to 5.5	-25 to +85		
μPD43256BGW-85X-9JL		85				
μPD43256BGW-A85X-9JL		85	3.0 to 5.5			A version
μPD43256BGW-A10X-9JL		100				
μPD43256BGW-A12X-9JL		120				
μPD43256BGW-B10X-9JL		100	2.7 to 5.5			B version
μPD43256BGW-B15X-9JL		150				
μPD43256BGW-70X-9JL-A	28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)	70	4.5 to 5.5			
μPD43256BGW-85X-9JL-A		85				
μPD43256BGW-A85X-9JL-A		85	3.0 to 5.5			A version
μPD43256BGW-A10X-9JL-A		100				
μPD43256BGW-A12X-9JL-A		120				
μPD43256BGW-B10X-9JL-A		100	2.7 to 5.5			B version

**Remark** Products with -A at the end of the part number are lead-free products.

Pin Configurations (Marking Side)

/xxx indicates active low signal.

28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)

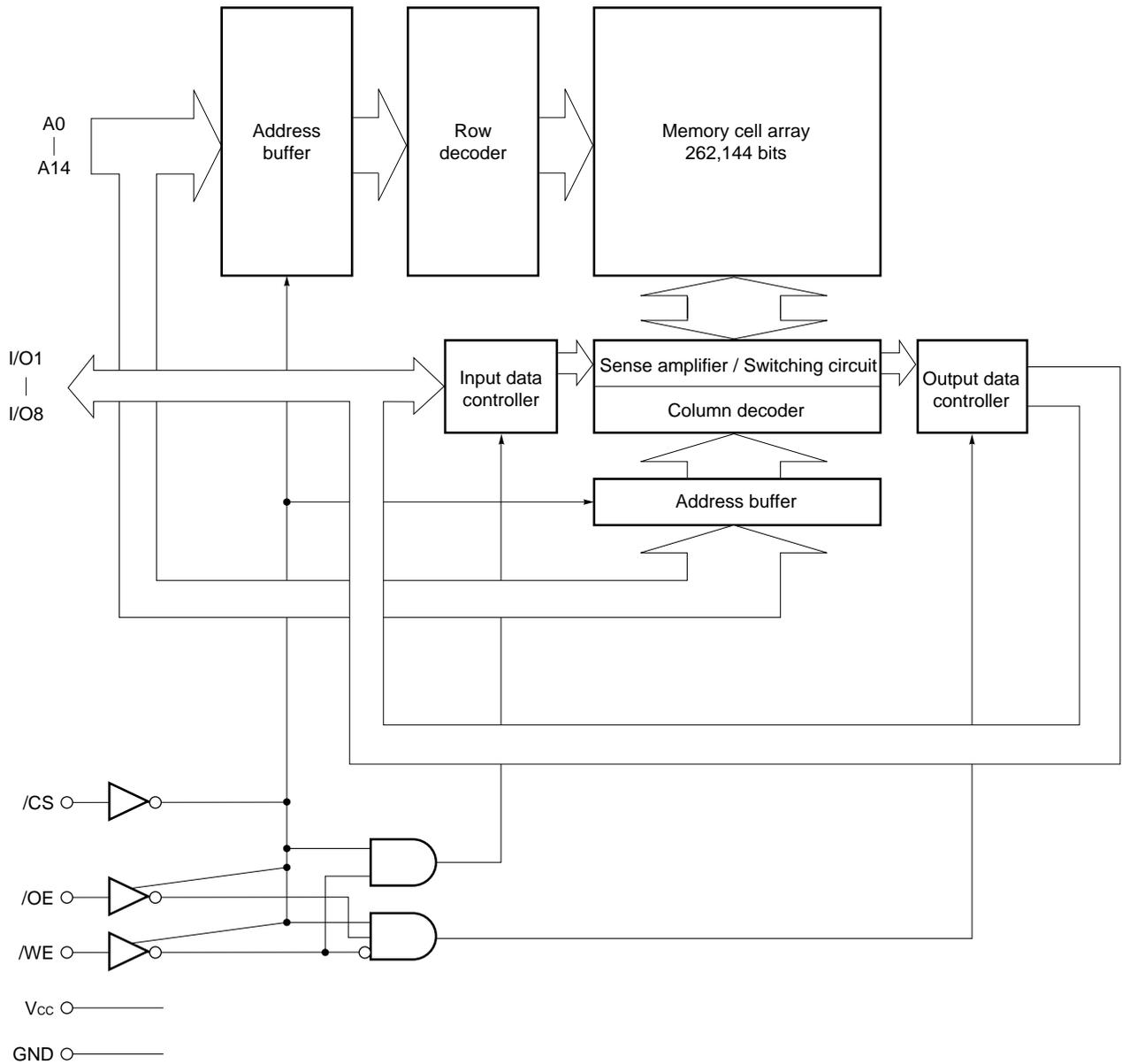
- [μPD43256BGW-xxX-9JL]
- [μPD43256BGW-AxxX-9JL]
- [μPD43256BGW-BxxX-9JL]
- [μPD43256BGW-xxX-9JL-A]
- [μPD43256BGW-AxxX-9JL-A]
- [μPD43256BGW-BxxX-9JL-A]



- |           |                         |                 |                 |
|-----------|-------------------------|-----------------|-----------------|
| A0 - A14  | : Address inputs        | /OE             | : Output Enable |
| /O1 - /O8 | : Data inputs / outputs | V <sub>CC</sub> | : Power supply  |
| /CS       | : Chip Select           | GND             | : Ground        |
| /WE       | : Write Enable          |                 |                 |

**Remark** Refer to **Package Drawings** for the 1-pin index mark.

Block Diagram



Truth Table

/CS	/OE	/WE	Mode	I/O	Supply current
H	×	×	Not selected	High impedance	I <sub>SB</sub>
L	H	H	Output disable		I <sub>CCA</sub>
L	×	L	Write	D <sub>IN</sub>	I <sub>CCA</sub>
L	L	H	Read	D <sub>OUT</sub>	

Remark × : V<sub>IH</sub> or V<sub>IL</sub>

**Electrical Specifications**

**Absolute Maximum Ratings**

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V <sub>CC</sub>		-0.5 <sup>Note</sup> to +7.0	V
Input / Output voltage	V <sub>T</sub>		-0.5 <sup>Note</sup> to V <sub>CC</sub> + 0.5	V
Operating ambient temperature	T <sub>A</sub>		-25 to +85	°C
Storage temperature	T <sub>stg</sub>		-55 to +125	°C

**Note** -3.0 V (MIN.) (Pulse width : 50 ns)

**Caution** Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

**Recommended Operating Conditions**

Parameter	Symbol	Condition	μPD43256B-xxX		μPD43256B-AxxX		μPD43256B-BxxX		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Supply voltage	V <sub>CC</sub>		4.5	5.5	3.0	5.5	2.7	5.5	V
High level input voltage	V <sub>IH</sub>		2.4	V <sub>CC</sub> +0.5	2.4	V <sub>CC</sub> +0.5	2.4	V <sub>CC</sub> +0.5	V
Low level input voltage	V <sub>IL</sub>		-0.3 <sup>Note</sup>	+0.6	-0.3 <sup>Note</sup>	+0.4	-0.3 <sup>Note</sup>	+0.4	V
Operating ambient temperature	T <sub>A</sub>		-25	+85	-25	+85	-25	+85	°C

**Note** -3.0 V (MIN.) (Pulse width: 50 ns)

**Capacitance (T<sub>A</sub> = 25°C, f = 1 MHz)**

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C <sub>IN</sub>	V <sub>IN</sub> = 0 V			5	pF
Input / Output capacitance	C <sub>I/O</sub>	V <sub>I/O</sub> = 0 V			8	pF

- Remarks**
- V<sub>IN</sub> : Input voltage  
V<sub>I/O</sub> : Input / Output voltage
  - These parameters are periodically sampled and not 100% tested.

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted) (1/2)

Parameter	Symbol	Test condition	μPD43256B-xxX			Unit
			MIN.	TYP.	MAX.	
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> = 0 V to V <sub>CC</sub>	-1.0		+1.0	μA
I/O leakage current	I <sub>LO</sub>	V <sub>I/O</sub> = 0 V to V <sub>CC</sub> , /OE = V <sub>IH</sub> or /CS = V <sub>IH</sub> or /WE = V <sub>IL</sub>	-1.0		+1.0	μA
Operating supply current	I <sub>CCA1</sub>	/CS = V <sub>IL</sub> , Minimum cycle time, I <sub>I/O</sub> = 0 mA			45	mA
	I <sub>CCA2</sub>	/CS = V <sub>IL</sub> , I <sub>I/O</sub> = 0 mA			15	
	I <sub>CCA3</sub>	/CS ≤ 0.2 V, Cycle = 1 MHz, I <sub>I/O</sub> = 0 mA, V <sub>IL</sub> ≤ 0.2 V, V <sub>IH</sub> ≥ V <sub>CC</sub> - 0.2 V			15	
Standby supply current	I <sub>SB</sub>	/CS = V <sub>IH</sub>			3	mA
	I <sub>SB1</sub>	/CS ≥ V <sub>CC</sub> - 0.2 V		1.0	50	
High level output voltage	V <sub>OH1</sub>	I <sub>OH</sub> = -1.0 mA	2.4			V
	V <sub>OH2</sub>	I <sub>OH</sub> = -0.1 mA	V <sub>CC</sub> -0.5			
Low level output voltage	V <sub>OL</sub>	I <sub>OL</sub> = 2.1 mA			0.4	V

Remarks 1. V<sub>IN</sub> : Input voltage

V<sub>I/O</sub> : Input / Output voltage

2. These DC characteristics are in common regardless of package types.

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted) (2/2)

Parameter	Symbol	Test condition	μPD43256B-AxxX			μPD43256B-BxxX			Unit
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> = 0 V to V <sub>CC</sub>	-1.0		+1.0	-1.0		+1.0	μA
I/O leakage current	I <sub>LO</sub>	V <sub>I/O</sub> = 0 V to V <sub>CC</sub> , /OE = V <sub>IH</sub> or /CS = V <sub>IH</sub> or /WE = V <sub>IL</sub>	-1.0		+1.0	-1.0		+1.0	μA
Operating supply current	I <sub>CCA1</sub>	/CS = V <sub>IL</sub> , Minimum cycle time, I <sub>I/O</sub> = 0 mA	μPD43256B-A85X			45		-	mA
			μPD43256B-A10X			40		-	
			μPD43256B-A12X			40		-	
			μPD43256B-B10X			-		40	
			μPD43256B-B15X			-		40	
	V <sub>CC</sub> ≤ 3.3 V			-		25			
	I <sub>CCA2</sub>	/CS = V <sub>IL</sub> , I <sub>I/O</sub> = 0 mA				15		15	
V <sub>CC</sub> ≤ 3.3 V				-		10			
I <sub>CCA3</sub>	/CS ≤ 0.2 V, Cycle = 1 MHz, I <sub>I/O</sub> = 0 mA, V <sub>IL</sub> ≤ 0.2 V, V <sub>IH</sub> ≥ V <sub>CC</sub> - 0.2 V				15		15		
		V <sub>CC</sub> ≤ 3.3 V			-		10		
Standby supply current	I <sub>SB</sub>	/CS = V <sub>IH</sub>				3		3	mA
			V <sub>CC</sub> ≤ 3.3 V			-		2	
	I <sub>SB1</sub>	/CS ≥ V <sub>CC</sub> - 0.2 V		1.0	50		1.0	50	μA
		V <sub>CC</sub> ≤ 3.3 V			-		25		
High level output voltage	V <sub>OH1</sub>	I <sub>OH</sub> = -1.0 mA, V <sub>CC</sub> ≥ 4.5 V		2.4		2.4		V	
		I <sub>OH</sub> = -0.5 mA, V <sub>CC</sub> < 4.5 V		2.4		2.4			
	V <sub>OH2</sub>	I <sub>OH</sub> = -0.02 mA		V <sub>CC</sub> - 0.1		V <sub>CC</sub> - 0.1			
Low level output voltage	V <sub>OL</sub>	I <sub>OL</sub> = 2.1 mA, V <sub>CC</sub> ≥ 4.5 V				0.4		V	
		I <sub>OL</sub> = 1.0 mA, V <sub>CC</sub> < 4.5 V				0.4			
	V <sub>OL1</sub>	I <sub>OL</sub> = 0.02 mA				0.1			

Remarks 1. V<sub>IN</sub> : Input voltage

V<sub>I/O</sub> : Input / Output voltage

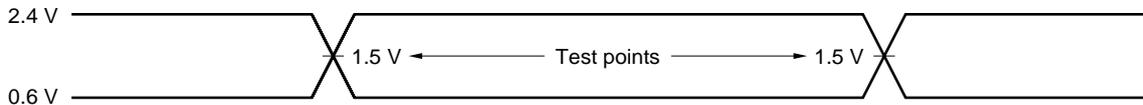
2. These DC characteristics are in common regardless of package types.

AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

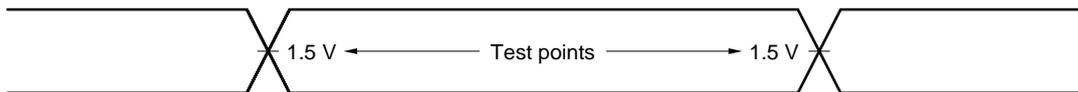
AC Test Conditions

[μPD43256B-70X, μPD43256B-85X]

Input Waveform (Rise and Fall Time ≤ 5 ns)



Output Waveform



Output Load

AC characteristics should be measured with the following output load conditions.

Figure 1

( $t_{AA}$ ,  $t_{ACS}$ ,  $t_{OE}$ ,  $t_{OH}$ )

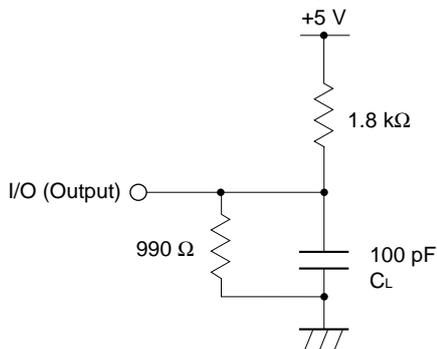
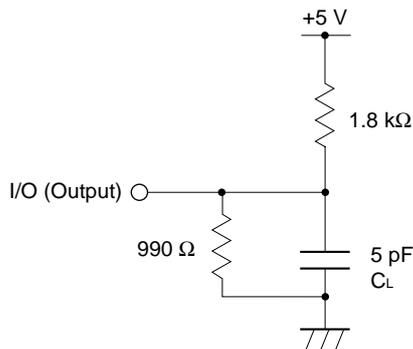


Figure 2

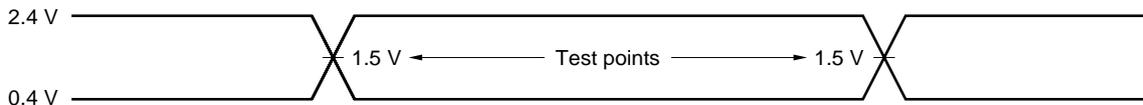
( $t_{CHZ}$ ,  $t_{CLZ}$ ,  $t_{OHZ}$ ,  $t_{OLZ}$ ,  $t_{WHZ}$ ,  $t_{OW}$ )



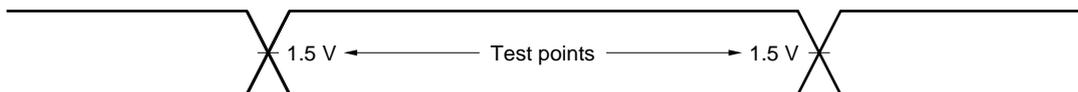
Remark  $C_L$  includes capacitance of the probe and jig, and stray capacitance.

[μPD43256B-A85X, μPD43256B-A10X, μPD43256B-A12X, μPD43256B-B10X, μPD43256B-B15X]

Input Waveform (Rise and Fall Time ≤ 5 ns)



Output Waveform



Output Load

AC characteristics should be measured with the following output load conditions.

$t_{AA}$ , $t_{ACS}$ , $t_{OE}$ , $t_{OH}$	$t_{CHZ}$ , $t_{CLZ}$ , $t_{OHZ}$ , $t_{OLZ}$ , $t_{WHZ}$ , $t_{OW}$
1TTL + 50 pF	1TTL + 5 pF

Read Cycle (1/2)

Parameter	Symbol	V <sub>CC</sub> ≥ 4.5 V						Unit	Con- dition
		μPD43256B-70X		μPD43256B-85X		μPD43256B-AxxX μPD43256B-BxxX			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t <sub>RC</sub>	70		85		100		ns	
Address access time	t <sub>AA</sub>		70		85		100	ns	<b>Note</b>
/CS access time	t <sub>ACS</sub>		70		85		100	ns	
/OE access time	t <sub>OE</sub>		35		40		50	ns	
Output hold from address change	t <sub>OH</sub>	10		10		10		ns	
/CS to output in low impedance	t <sub>CLZ</sub>	10		10		10		ns	
/OE to output in low impedance	t <sub>OLZ</sub>	5		5		5		ns	
/CS to output in high impedance	t <sub>CHZ</sub>		30		30		35	ns	
/OE to output in high impedance	t <sub>OHZ</sub>		30		30		35	ns	

**Note** See the **output load**.

**Remark** These AC characteristics are in common regardless of package types and L, LL versions.

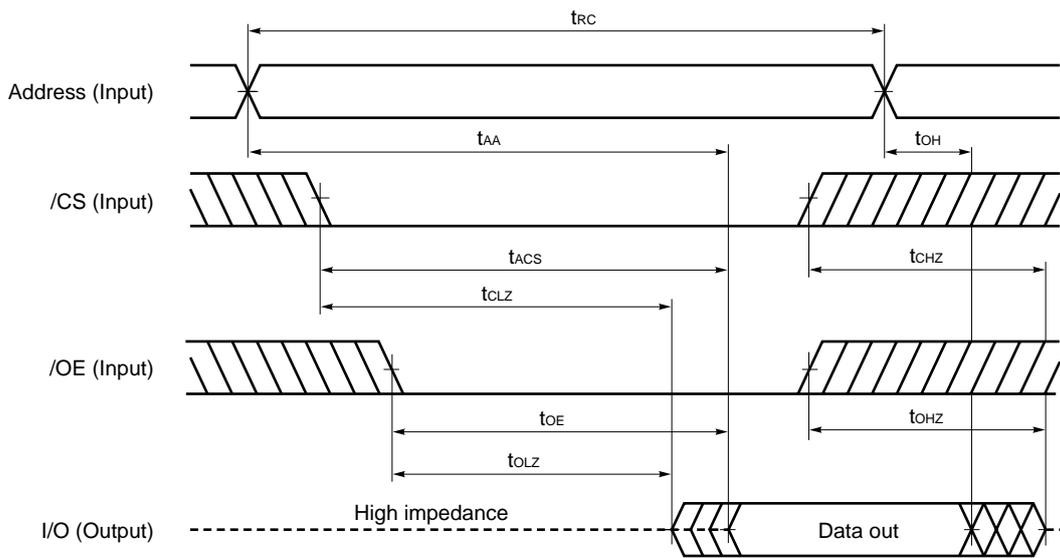
Read Cycle (2/2)

Parameter	Symbol	V <sub>CC</sub> ≥ 3.0 V						V <sub>CC</sub> ≥ 2.7 V				Unit	Con- dition
		μPD43256B-A85X		μPD43256B-A10X		μPD43256B-A12X		μPD43256B-B10X		μPD43256B-B15X			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t <sub>RC</sub>	85		100		120		100		150		ns	
Address access time	t <sub>AA</sub>		85		100		120		100		150	ns	<b>Note</b>
/CS access time	t <sub>ACS</sub>		85		100		120		100		150	ns	
/OE access time	t <sub>OE</sub>		50		60		60		60		70	ns	
Output hold from address change	t <sub>OH</sub>	10		10		10		10		10		ns	
/CS to output in low impedance	t <sub>CLZ</sub>	10		10		10		10		10		ns	
/OE to output in low impedance	t <sub>OLZ</sub>	5		5		5		5		5		ns	
/CS to output in high impedance	t <sub>CHZ</sub>		35		35		40		35		50	ns	
/OE to output in high impedance	t <sub>OHZ</sub>		35		35		40		35		50	ns	

**Note** See the **output load**.

**Remark** These AC characteristics are in common regardless of package types.

Read Cycle Timing Chart



**Remark** In read cycle, /WE should be fixed to high level.

**Write Cycle (1/2)**

Parameter	Symbol	V <sub>CC</sub> ≥ 4.5 V						Unit	Con- dition
		μPD43256B-70X		μPD43256B-85X		μPD43256B-AxxX μPD43256B-BxxX			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	t <sub>wc</sub>	70		85		100		ns	
/CS to end of write	t <sub>cw</sub>	60		70		80		ns	
Address valid to end of write	t <sub>AW</sub>	60		70		80		ns	
Write pulse width	t <sub>WP</sub>	55		60		70		ns	
Data valid to end of write	t <sub>DW</sub>	30		35		40		ns	
Data hold time	t <sub>DH</sub>	5		5		5		ns	
Address setup time	t <sub>AS</sub>	0		0		0		ns	
Write recovery time	t <sub>WR</sub>	0		0		0		ns	
/WE to output in high impedance	t <sub>WHZ</sub>		30		30		35	ns	<b>Note</b>
Output active from end of write	t <sub>OW</sub>	5		5		5		ns	

**Note** See the **output load**.

**Remark** These AC characteristics are in common regardless of package types and L, LL versions.

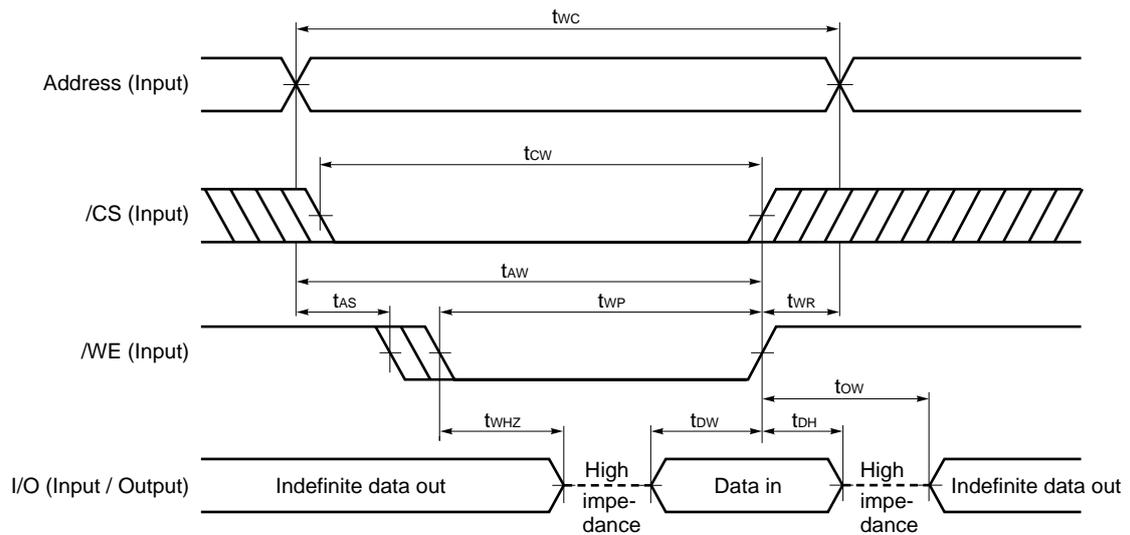
**Write Cycle (2/2)**

Parameter	Symbol	V <sub>CC</sub> ≥ 3.0 V						V <sub>CC</sub> ≥ 2.7 V				Unit	Con- dition
		μPD43256B-A85X		μPD43256B-A10X		μPD43256B-A12X		μPD43256B-B10X		μPD43256B-B15X			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	t <sub>wc</sub>	85		100		120		100		150		ns	
/CS to end of write	t <sub>cw</sub>	70		70		90		70		100		ns	
Address valid to end of write	t <sub>AW</sub>	70		70		90		70		100		ns	
Write pulse width	t <sub>WP</sub>	60		60		80		60		90		ns	
Data valid to end of write	t <sub>DW</sub>	60		60		70		60		80		ns	
Data hold time	t <sub>DH</sub>	5		5		5		5		5		ns	
Address setup time	t <sub>AS</sub>	0		0		0		0		0		ns	
Write recovery time	t <sub>WR</sub>	0		0		0		0		0		ns	
/WE to output in high impedance	t <sub>WHZ</sub>		35		35		40		35		40	ns	<b>Note</b>
Output active from end of write	t <sub>OW</sub>	5		5		5		5		5		ns	

**Note** See the **output load**.

**Remark** These AC characteristics are in common regardless of package types.

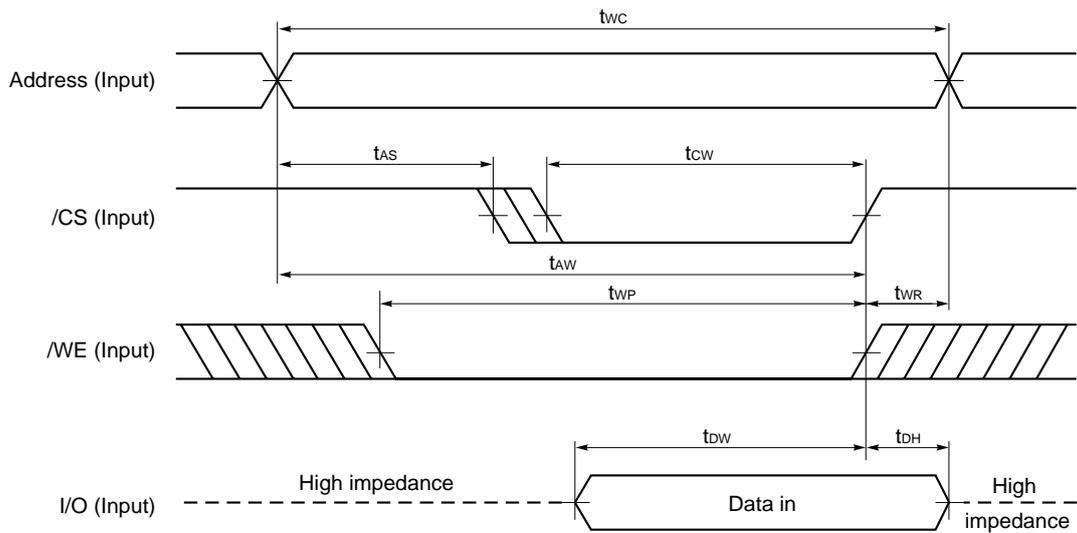
**Write Cycle Timing Chart 1 (/WE Controlled)**



- Cautions**
1. /CS or /WE should be fixed to high level during address transition.
  2. When I/O pins are in the output state, do not apply to the I/O pins signals that are opposite in phase with output signals.

- Remarks**
1. Write operation is done during the overlap time of a low level /CS and a low level /WE.
  2. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.
  3. If /CS changes to low level at the same time or after the change of /WE to low level, the I/O pins will remain high impedance state.

**Write Cycle Timing Chart 2 (/CS Controlled)**



- Cautions**
1. /CS or /WE should be fixed to high level during address transition.
  2. When I/O pins are in the output state, do not apply to the I/O pins signals that are opposite in phase with output signals.

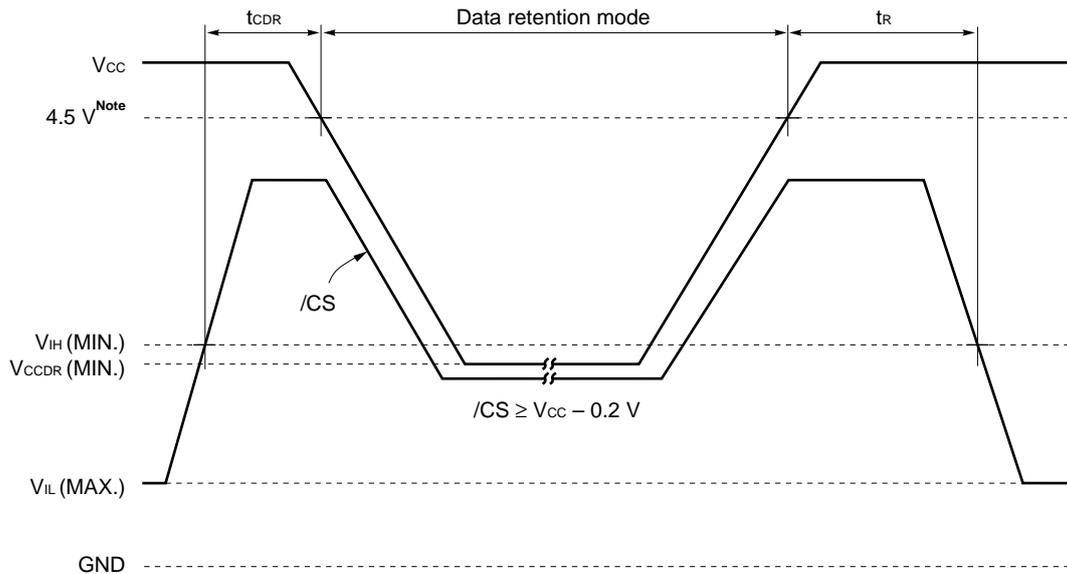
**Remark** Write operation is done during the overlap time of a low level /CS and a low level /WE.

**Low V<sub>CC</sub> Data Retention Characteristics (T<sub>A</sub> = -25 to +85 °C)**

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V <sub>CDDR</sub>	/CS ≥ V <sub>CC</sub> - 0.2 V	2.0		5.5	V
Data retention supply current	I <sub>CDDR</sub>	V <sub>CC</sub> = 3.0 V, /CS ≥ V <sub>CC</sub> - 0.2 V		0.5	20 <sup>Note</sup>	μA
Chip deselection to data retention mode	t <sub>CDR</sub>		0			ns
Operation recovery time	t <sub>R</sub>		5			ms

**Note** 2 μA (T<sub>A</sub> ≤ 40 °C), 7 μA (T<sub>A</sub> ≤ 70 °C)

**Data Retention Timing Chart**

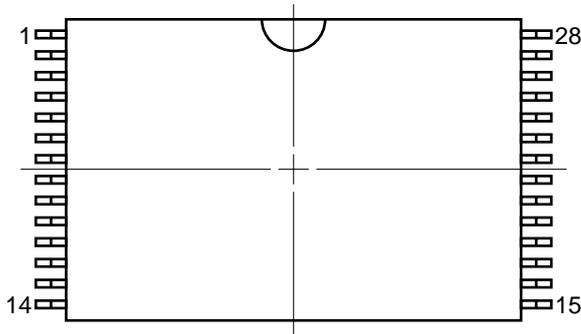


**Note** A version : 3.0 V, B version : 2.7 V

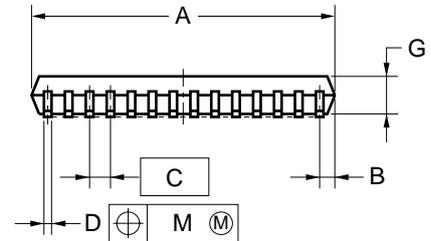
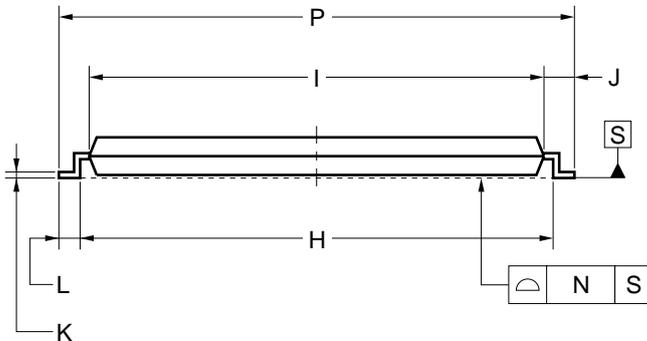
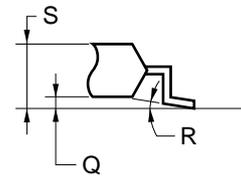
**Remark** The other pins (Address, /OE, /WE, I/O) can be in high impedance state.

Package Drawings

28-PIN PLASTIC TSOP(I) (8x13.4)



detail of lead end



NOTES

1. Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.
2. "A" excludes mold flash. (Includes mold flash : 8.4mm MAX.)

ITEM	MILLIMETERS
A	8.0±0.1
B	0.6 MAX.
C	0.55 (T.P.)
D	0.22 <sup>+0.08</sup> <sub>-0.07</sub>
G	1.0
H	12.4±0.2
I	11.8±0.1
J	0.8±0.2
K	0.145 <sup>+0.025</sup> <sub>-0.015</sub>
L	0.5±0.1
M	0.08
N	0.10
P	13.4±0.2
Q	0.1±0.05
R	3° <sup>+7°</sup> <sub>-3°</sub>
S	1.2 MAX.

P28GW-55-9JL-2

**Recommended Soldering Conditions**

Please consult with our sales offices for soldering conditions of the  $\mu$ PD43256B-X.

**Types of Surface Mount Device**

$\mu$ PD43256BGW-xxX-9JL	: 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)
$\mu$ PD43256BGW-AxxX-9JL	: 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)
$\mu$ PD43256BGW-BxxX-9JL	: 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)
$\mu$ PD43256BGW-xxX-9JL-A	: 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)
$\mu$ PD43256BGW-AxxX-9JL-A	: 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)
$\mu$ PD43256BGW-BxxX-9JL-A	: 28-pin PLASTIC TSOP(I) (8x13.4) (Normal bent)

**Revision History**

Edition/ Date	Page		Type of revision	Description
	This edition	Previous edition		
7th edition/ Nov. 2008	through	through	Modification	Ordering Information revised.

[MEMO]

## NOTES FOR CMOS DEVICES

**① VOLTAGE APPLICATION WAVEFORM AT INPUT PIN**

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between  $V_{IL}$  (MAX) and  $V_{IH}$  (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between  $V_{IL}$  (MAX) and  $V_{IH}$  (MIN).

**② HANDLING OF UNUSED INPUT PINS**

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to  $V_{DD}$  or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

**③ PRECAUTION AGAINST ESD**

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

**④ STATUS BEFORE INITIALIZATION**

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

**⑤ POWER ON/OFF SEQUENCE**

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

**⑥ INPUT OF SIGNAL DURING POWER OFF STATE**

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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